TOSHIBA Transistor Silicon NPN Triple Diffused Type (Darlington Power Transistor)

2SD2449

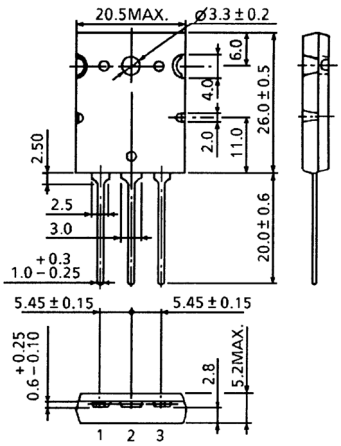
Power Amplifier Applications

- High breakdown voltage: V_{CEO} = 160 V (min)
- Complementary to 2SB1594

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	160	V
Collector-emitter voltage	V_{CEO}	160	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	10	A
Base current	I_B	1	A
Collector power dissipation (Tc = 25°C)	P_C	150	W
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55 to 150	°C

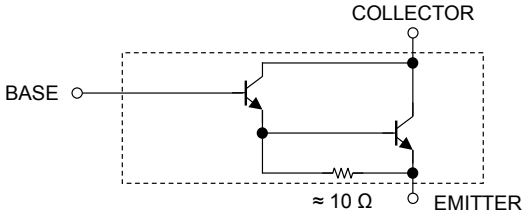
Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-21F1A

Weight: 9.75 g (typ.)

Equivalent Circuit

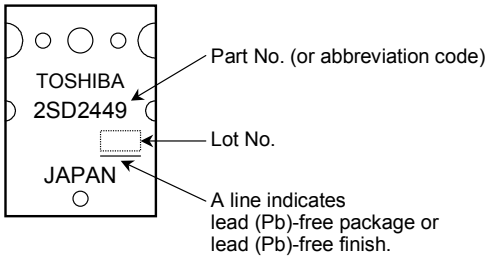


Electrical Characteristics (Ta = 25°C)

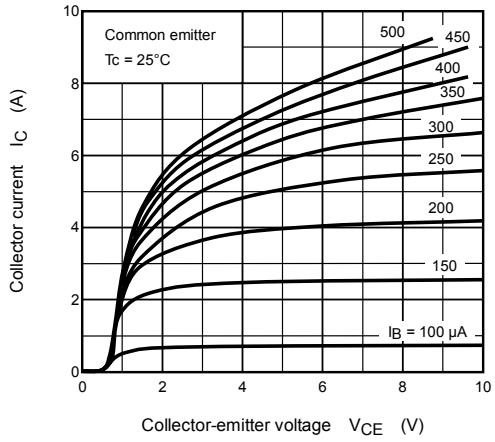
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 160 V, I_E = 0	—	—	5	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 5 V, I_C = 0	—	—	5	μA
Collector-emitter breakdown voltage	$V_{(BR)\ CEO}$	I_C = 50 mA, I_B = 0	160	—	—	V
DC current gain	$h_{FE\ (1)}$ (Note)	V_{CE} = 5 V, I_C = 8 A	3000	—	20000	
	$h_{FE\ (2)}$	V_{CE} = 5 V, I_C = 12 A	2000	—	—	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = 8 A, I_B = 8 mA	—	—	3.0	V
Base-emitter voltage	V_{BE}	V_{CE} = 5 V, I_C = 8 A	—	—	3.0	V
Transition frequency	f_T	V_{CE} = 5 V, I_C = 1 A	—	30	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz	—	150	—	pF

Note: $h_{FE\ (1)}$ classification A: 3000 to 10000, B: 5000 to 15000, C: 7000 to 20000

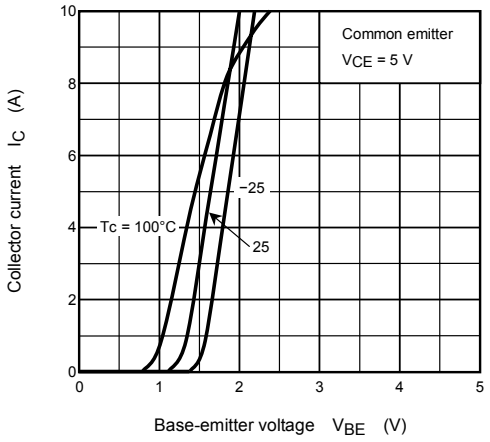
Marking



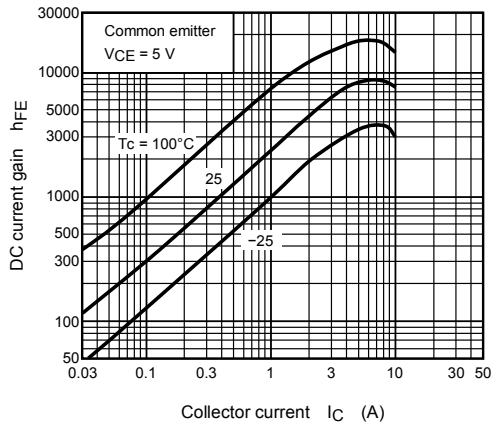
$I_C - V_{CE}$



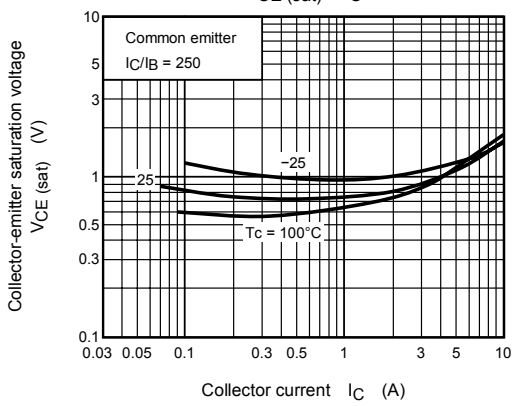
$I_C - V_{BE}$



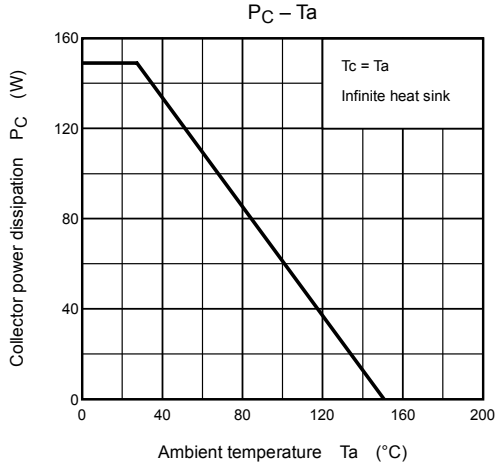
$h_{FE} - I_C$



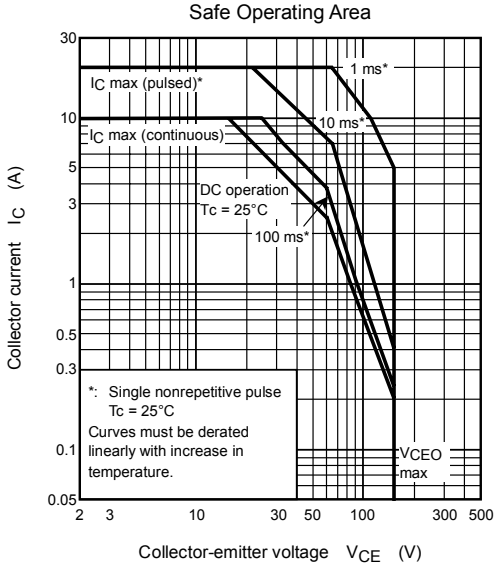
$V_{CE\ (sat)} - I_C$



$P_C - Ta$



Safe Operating Area



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